

HIGH-SPEED 3.3V 1K X 8 DUAL-PORT STATIC RAM

IDT71V30S/L

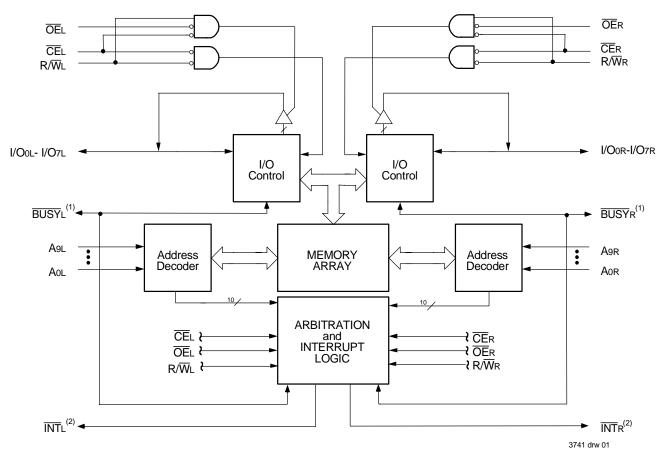
LEAD FINISH (SnPb) ARE IN EOL PROCESS - LAST TIME BUY EXPIRES JUNE 15, 2018

Features

- High-speed access
 - Commercial: 25/35/55ns (max.)
 - Industrial 35ns (max.)
- Low-power operation
 - IDT71V30S
 - Active: 375mW (typ.)
 - Standby: 5mW (typ.)
 - IDT71V30L
 - Active: 375mW (typ.) Standby: 1mW (typ.)

- On-chip port arbitration logic
- Interrupt flags for port-to-port communication
- Fully asynchronous operation from either port
- Battery backup operation, 2V data retention (L Only)
- * TTL-compatible, single 3.3V ±0.3V power supply
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Green parts available, see ordering information

Functional Block Diagram



NOTES:

- 1. IDT71V30: BUSY outputs are non-tristatable push-pulls.

DECEMBER 2017

Description

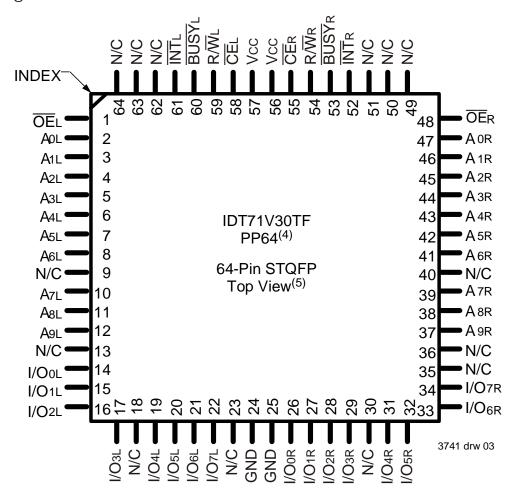
The IDT71V30 is a high-speed 1K x 8 Dual-Port Static RAM. The IDT71V30 is designed to be used as a stand-alone 8-bit Dual-Port SRAM.

Both devices provide two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by \overline{CE} , permits the on chip circuitry of each port to enter a very low standby power mode.

Fabricated using CMOS high-performance technology, these devices typically operate on only 375mW of power. Low-power (L) versions offer battery backup data retention capability, with each Dual-Port typically consuming 200µW from a 2V battery.

The IDT71V30 devices are packaged in 64-pin STQFPs.

Pin Configurations (1,2,3)



- 1. All Vcc pins must be connected to the power supply.
- 2. All GND pins must be connected to the ground supply.
- 3. Package body is approximately 10mm x 10mm x 1.4mm.
- This package code is used to reference the package diagram.
- This text does not indicate the orientation of the actual part-marking.

Absolute Maximum Ratings(1)

Symbol	Rating	Com'l & Ind	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.60	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	°C
TJN ⁽³⁾	Junction Temperature	+150	۰C
Іоит	DC Output Current	50	mA

NOTES: 3741 tbl 01

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS
 may cause permanent damage to the device. This is a stress rating only
 and functional operation of the device at these or any other conditions
 above those indicated in the operational sections of the specification is not
 implied. Exposure to absolute maximum rating conditions for extended
 periods may affect reliability.
- VTERM must not exceed Vcc + 0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to < 20mA for the period of VTERM > Vcc + 0.3V.
- 3. This is the absolute maximum junction temperature for the device. No DC Bias.

Capacitance⁽¹⁾ (TA = +25°C, f=1.0MHz)

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	9	pF
Cout ⁽³⁾	Output Capacitance	Vout = 3dV	10	pF

NOTES:

- This parameter is determined by device characterization but is not production tested.
- 3dv references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	3.0	3.3	3.6	V
GND	Ground	0	0	0	V
V⊪	Input High Voltage	2.0	_	Vcc+0.3V	V
VIL	Input Low Voltage	-0.3 ⁽¹⁾	_	0.8	V

NOTE:

NOTES:

1. V_{IL} (min.) = -1.5V for pulse width less than 20ns.

Maximum Operating Temperature and Supply Voltage^(1,2)

Grade	Ambient Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3

3741 tbl 03

- 1. This is the parameter Ta. This is the "instant on" case temperature.
- 2. Industrial temperature: for specific speeds, packages and powers, contact your sales office.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 3.3V ± 0.3V)

•			71V30S		71V		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
ILI	Input Leakage Current ⁽¹⁾	Vcc = 3.6V, Vin = 0V to Vcc	_	10	_	5	μA
llo	Output Leakage Current	CE = VIH, VOUT = 0V to VCC	_	10	_	5	μΑ
Vol	Output Low Voltage (I/Oo-I/O7)	IOL = 4mA	_	0.4	_	0.4	V
Voh	Output High Voltage	Iон = -4mA	2.4	_	2.4	_	V

NOTE:

3741 tbl 05

3741 thl 02

1. At Vcc ≤ 2.0V input leakages are undefined.

DC Electrical Characteristics Over the Operating

Temperature and Supply Voltage Range (1,6,7) (Vcc = 3.3V ± 0.3V)

		Tuppiy voitage is			71V30 Com'l		71V3 Com'l		71V3(Com'l			
Symbol	Parameter	Test Condition	Versi	on	Typ. ⁽²⁾	Max.	Typ. ⁽²⁾	Max.	Typ. ⁽²⁾	Max.	Unit	
lcc	Dynamic Operating Current (Both Ports Active)	CEL and CER = VIL, Outputs Disabled $f = f_{MAX}^{(3)}$	COM'L	S L	75 75	150 120	75 75	145 115	75 75	135 105	mA	
		T = IMAC.	IND	S L		1 1	— 75	_ 145	1 1			
ISB1	Standby Current (Both Ports - TTL Level	CEL and CER= VIL, $f = f_{MAX}^{(3)}$	COM'L	S L	20 20	50 35	20 20	50 35	20 20	50 35	mA	
	Inputs)		INE	IND	S L		-	 20	— 50			
ISB2	Standby Current (One Port - TTL Level Inputs)		COM'L	S L	30 30	105 75	30 30	100 70	30 30	90 60	mA	
			IND	S L	_ _	-	_ 30	_ 100	_ _	-		
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	CEL and CER \geq Vcc - 0.2V Vin \geq Vcc - 0.2V or Vin \leq 0.2V, f = 0 ⁽⁴⁾	COM'L	S L	1.0 0.2	5.0 3.0	1.0 0.2	5.0 3.0	1.0 0.2	5.0 3.0	mA	
		VIN ≤ 0.2V, I = 0.7	IND	S L	_	-	_ 1.0	_ 5.0	-			
ISB4	Full Standby Current (One Port - CMOS	CE"B" > Vcc - 0.2V and CE"B" > Vcc - 0.2V(5)	COM'L	S L	30 30	90 75	30 30	85 70	30 30	75 60	mA	
	Level Inputs)	vel Inputs) $ V_{\mathbb{N}} \geq V_{\mathbb{C}C} - 0.2V \text{ or } V_{\mathbb{N}} \leq 0.2V $ Active Port Outputs Disabled $ f_{=fmax}^{(3)} $	IND	S L	_ _		 30	— 85	_ _	_		

3741 tbl 06

NOTES:

- 1. 'X' in part number indicates power rating (S or L)
- 2. Vcc = 3.3V, TA = +25°C, and are not production tested. Iccdc = 70mA (Typ.)
- 3. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc.
- 4. f = 0 means no address or control lines change.
- 5. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 6. Refer to chip enable Truth Table I.
- 7. Industrial temperature: for specific speeds, packages and powers contact your sales office.

Data Retention Characteristics (L Version Only)

				71V30L			
Symbol	Parameter	Test Condition	Min.	Typ. ⁽¹⁾	Max.	Unit	
VDR	Vcc for Data Retention			2.0	_	_	V
ICCDR	Data Retention Current		Ind.		100	1000	μΑ
		$Vcc = 2V, \overline{CE} \ge Vcc -0.2V$	Com'l.	_	100	500	
tcdr ⁽³⁾	Chip Deselect to Data Retention Time	$Vin \ge Vcc -0.2V \text{ or } Vin \le 0.2V$		0	_	_	ns
tR ⁽³⁾	Operation Recovery Time			trc(2)	_	_	ns

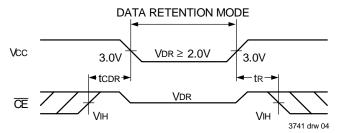
3741 tbl 07

- 1. Vcc = 2V, Ta = +25°C, and is not production tested.
- 2. trc = Read Cycle Time.
- 3. This parameter is guaranteed by device characterization but not production tested.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1 and 2

Data Retention Waveform



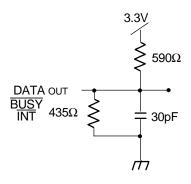


Figure 1. AC Output Test Load

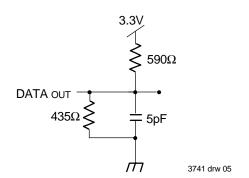


Figure 2. Output Test Load (For thz, thz, twz and tow)
* Including scope and jig.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(3,4)

		71V30X25 Com'l Only		71V30X35 Com'l & Ind		71V30X55 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYC	CLE							
trc	Read Cycle Time	25	_	35		55	_	ns
taa	Address Access Time	_	25	_	35		55	ns
tace	Chip Enable Access Time		25	_	35		55	ns
taoe	Output Enable Access Time	_	12	_	20		25	ns
tон	Output Hold from Address Change	3	_	3		3	_	ns
tLZ	Output Low-Z Time ^(1,2)	0	_	0		0	_	ns
tHZ	Output High-Z Time ^(1,2)	_	12	_	15		30	ns
tpu	Chip Enable to Power Up Time ⁽²⁾	0		0		0		ns
tpD	Chip Disable to Power Down Time ⁽²⁾		50		50		50	ns

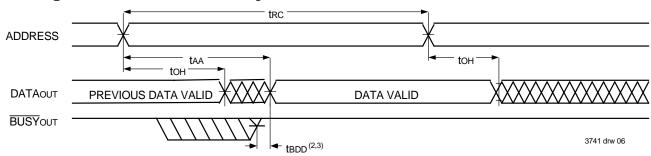
3741 tbl 08

NOTES:

- 1. Transition is measured 0mV from Low- or High-impedance voltage with Output Test Load (Figure 2).
- 2. This parameter is guaranteed by device characterization, but is not production tested.
- 3. 'X' in part number indicates power rating (S or L).
- 4. Industrial temperature: for specific speeds, packages and power contact your sales office.

3741 tbl 09

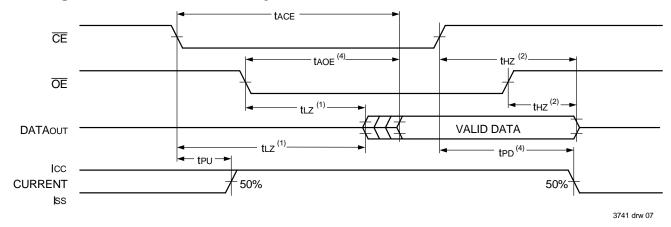
Timing Waveform of Read Cycle No. 1, Either Side⁽¹⁾



NOTES:

- 1. $R/\overline{W} = V_{IH}$, $\overline{CE} = V_{IL}$, and is $\overline{OE} = V_{IL}$. Address is valid prior to the coincidental with \overline{CE} transition LOW.
- 2. tbbb delay is required only in case where the opposite is port is completing a write operation to same the address location. For simultaneous read operations BUSY has no relationship to valid output data.
- 3. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA, and tBDD.

Timing Waveform of Read Cycle No. 2, Either Side⁽³⁾



- 1. Timing depends on which signal is asserted last, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 2. Timing depends on which signal is desserted first, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 3. $R/\overline{W} = VIH$ and the address is valid prior to or coincidental with \overline{CE} transition LOW.
- 4. Start of valid data depends on which timing becomes effective last tAOE, tACE, and tBDD.

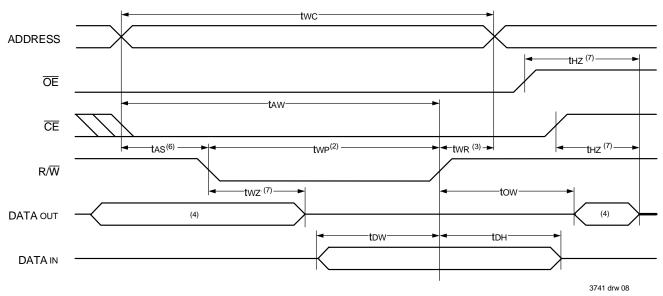
AC Electrical Characteristics Over the Operating Temperature and Supply Voltage^(4,5)

			0X25 I Only		0X35 & Ind	71V30X55 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CY	CLE							
twc	Write Cycle Time	25		35	_	55	_	ns
tew	Chip Enable to End-of-Write	20		30	_	40		ns
taw	Address Valid to End-of-Write	20		30	_	40		ns
tas	Address Set-up Time	0		0	_	0	_	ns
twp	Write Pulse Width	20		30	_	40		ns
twr	Write Recovery Time	0		0	_	0		ns
tow	Data Valid to End-of-Write	12		20	_	20	_	ns
tHZ	Output High-Z Time ^(1,2)		12		15		30	ns
tDH	Data Hold Time ⁽³⁾	0		0	_	0	_	ns
twz	Write Enable to Output in High-Z ^(1,2)	_	15	_	15	_	30	ns
tow	Output Active from End-of-Write ^(1,2,3)	0		0		0		ns

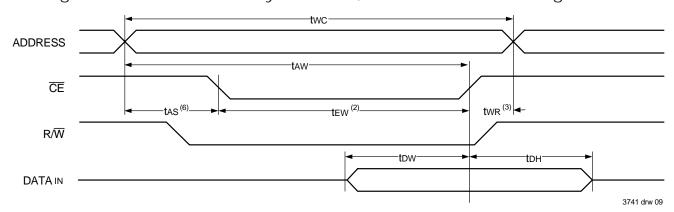
3741 tbl 10

- 1. Transition is measured 0mV from Low- or High-impedance voltage with Output Test Load (Figure 2).
- 2. This parameter is guaranteed by device characterization, but is not production tested.
- 3. The specification for tDH must be met by the device supplying write data to the SRAM under all operating conditions. Although tDH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.
- 4. 'X' in part number indicates power rating (S or L).
- 5. Industrial temperatures: for specific speeds, packages and powers contact your sales office.

Timing Waveform of Write Cycle No. 1,(R/W Controlled Timing)(1,5,8)



Timing Waveform of Write Cycle No. 2, **CE** Controlled Timing^(1,5)



- 1. $\ \ R/\overline{W}$ or $\overline{\text{CE}}$ must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of $\overline{\text{CE}}$ = V_{IL} and R/ $\overline{\text{W}}$ = V_{IL}.
- 3. twn is measured from the earlier of $\overline{\text{CE}}$ or R/\overline{W} going HIGH to the end of the write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE LOW transition occurs simultaneously with or after the R/W LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal $(\overline{CE} \text{ or } R/\overline{W})$ is asserted last.
- 7. This parameter is determined be device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If $\widetilde{\mathsf{OE}}$ is LOW during a R $\overline{\mathsf{W}}$ controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If $\overline{\mathsf{OE}}$ is HIGH during a R $\overline{\mathsf{W}}$ controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

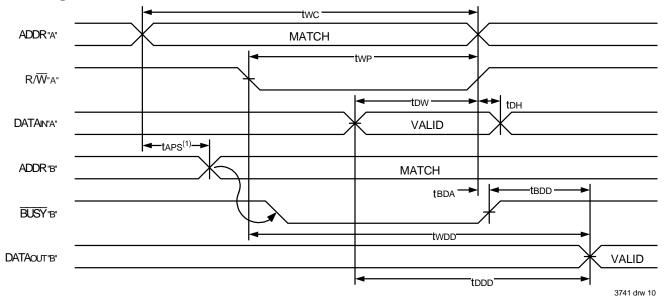
AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(6,7)

		71V30X25 Com'l Only		71V30X35 Com'l & Ind		71V30X55 Com'l Only			
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	
BUSY TIMING (M/S=Vih)									
tbaa	BUSY Access Time from Address Match		20		20		30	ns	
tbda	BUSY Disable Time from Address Not Matched	_	20		20		30	ns	
tbac	BUSY Access Time from Chip Enable		20		20		30	ns	
tBDC	BUSY Disable Time from Chip Enable		20		20	_	30	ns	
twn	Write Hold After BUSY ⁽⁵⁾	20	_	30		40		ns	
twdd	Write Pulse to Data Delay ⁽¹⁾	_	50	_	60		80	ns	
todo	Write Data Valid to Read Data Delay ⁽¹⁾	_	35	_	45		65	ns	
taps	Arbitration Priority Set-up Time ⁽²⁾	5	_	5		5		ns	
tBDD	BUSY Disable to Valid Data ⁽³⁾	_	30		30		45	ns	

NOTES: 3741 tbl 11

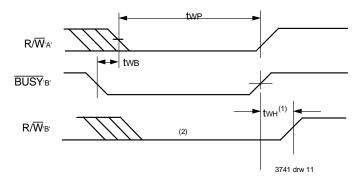
- 1. Port-to-port delay through SRAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read with BUSY".
- 2. To ensure that the earlier of the two ports wins.
- 3. tbdd is a calculated parameter and is the greater of 0, twdd twp (actual) or tddd tdw (actual).
- 4. To ensure that the Write Cycle is inhibited on Port "B" during contention on Port "A".
- 5. To ensure that the Write Cycle is completed on Port "B" after contention on Port "A".
- 6. 'X' in part number indicates power rating (S or L).
- 7. Industrial temperature: for specific speeds, packages and powers contact your sales office.

Timing Waveform of Write with Port-to-Port Read with **BUSY**(1,2,3,4)



- 1. To ensure that the earlier of the two ports wins.
- 2. $\overline{CE}L = \overline{CE}R = VIL$
- 3. \overline{OE} = VIL for the reading port.
- 4. All timing is the same for the left and right ports. Port 'A' may be either the left or right port. Port "B" is opposite from port "A".

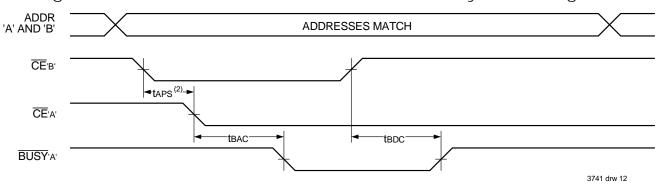
Timing Waveform of Write with **BUSY**(3)



NOTES:

- 1. twn must be met for BUSY.
- 2. BUSY is asserted on port 'B' blocking R/W'B', until BUSY'B' goes HIGH.
- 3. All timing is the same for the left and right ports. Port 'A' may be either the left or right port. Port "B" is opposite from port "A".

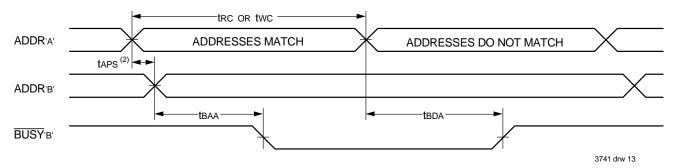
Timing Waveform of **BUSY** Arbitration Controlled by **CE** Timing⁽¹⁾



NOTES:

- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. If taps is not satisified, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted.

Timing Waveform of **BUSY** Arbitration Controlled Address Match Timing⁽¹⁾



- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. If taps is not satisified, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted.

AC Electrical Characteristics Over the

Operating Temperature and Supply Voltage Range^(1,2)

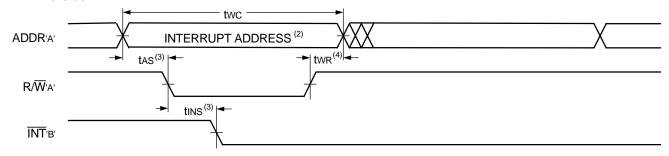
0 0 0		7.5 : 5::ag5 : tai:g6								
		71V30X25 Com'l Only		_	71V30X35 71V30X Com'l & Ind Com'l O					
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit		
INTERRUPT TIMING										
tas	Address Set-up Time	0	_	0		0		ns		
twr	Write Recovery Time	0	_	0		0		ns		
tins	Interrupt Set Time		25		25		45	ns		
tinr	Interrupt Reset Time		25	_	25		45	ns		

NOTES:

- 1. 'X' in part number indicates power rating (S or L).
- 2. Industrial temperature: for specific speeds, packages and powers contact your sales office.

Timing Waveform of Interrupt Mode⁽¹⁾

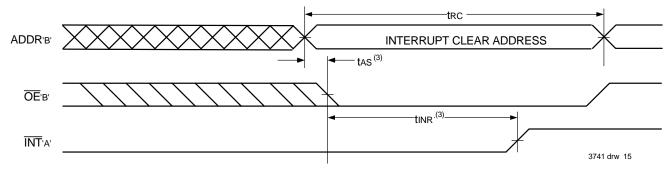
INT Sets



3741 drw 14

3741 tbl 12

INT Clears



- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. See Interrupt Truth Table II.
- 3. Timing depends on which enable signal ($\overline{\text{CE}}$ or R/\overline{W}) is asserted last.
- 4. Timing depends on which enable signal $(\overline{CE} \text{ or } R/\overline{W})$ is de-asserted first.

Truth Tables

Table I — Non-Contention Read/Write Control⁽⁴⁾

Left or Right Port (1)							
R/W	CE	ŌĒ	D0-7	Function			
Х	Н	Х	Z	Port Disabled and in Power-Down Mode, ISB2 or ISB4			
Х	Н	Х	Z	CER = CEL = VIH, Power-Down Mode, ISB1 or ISB3			
L	L	Х	DATAN	Data on Port Written Into Memory ⁽²⁾			
Н	L	L	DATAout	Data in Memory Output on Port ⁽³⁾			
Н	L	Н	Z	High Impedance Outputs			

NOTES: 3741 tbl 13

- 1. $A0L A9L \neq A0R A9R$.
- 2. If $\overline{BUSY} = L$, data is not written.
- 3. If $\overline{BUSY} = L$, data may not be valid, see two and tood timing.
- 4. 'H' = VIH, 'L' = VIL, 'X' = DON'T CARE, 'Z' = HIGH IMPEDANCE

Table II — Interrupt Flag^(1,4)

Left Port					Right Port					
R/₩L	CEL	<u>OE</u> L	A9L-A0L	ĪNT∟	R/W̄R	CER	ŌĒ R	A9R-A0R	Ī NT R	Function
L	L	Х	3FF	Х	Х	Х	Х	Х	L ⁽²⁾	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	3FF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	3FE	Х	Set Left INTL Flag
Х	L	L	3FE	H ⁽²⁾	Х	Х	Х	Χ	Х	Reset Left INTL Flag

NOTES: 3741 tbl 14

- 1. Assumes $\overline{BUSY}L = \overline{BUSY}R = VIH$
- 2. If $\overline{BUSY}L = VIL$, then No Change.
- 3. If $\overline{BUSY}R = VIL$, then No Change.
- 4. 'H' = HIGH,' L' = LOW,' X' = DON'T CARE

Table III — Address **BUSY** Arbitration

	In	puts	Out	puts	
CE L	CE _R	Aol-A9l Aor-A9r	BUSY _L (1)	BUSY _R (1)	Function
Χ	Χ	NO MATCH	Н	Н	Normal
Н	Χ	MATCH	Н	Н	Normal
Χ	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

3741 tbl 15

- Pins BUSYL and BUSYR are both outputs for IDT71V30. BUSYx outputs on the IDT71V30 are non-tristatable push-pull.
- 'L' if the inputs to the opposite port were stable prior to the address and enable inputs
 of this port. 'H' if the inputs to the opposite port became stable after the address and
 enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR = LOW will result.
 BUSYL and BUSYR outputs can not be LOW simultaneously.
- Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

Functional Description

The IDT71V30 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT71V30 has an automatic power down feature controlled by CE. The CE controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected $(\overline{\text{CE}} = \text{V}_{\text{H}})$. When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag ($\overline{\text{INTL}}$) is asserted when the right port writes to memory location 3FE (HEX), where a write is defined as the $\overline{\text{CE}} = R/\overline{W} = V_{\text{IL}}$ per Truth Table II. The left port clears the interrupt by accessing address location 3FE access with $\overline{\text{CE}}R = \overline{\text{OE}}R = V_{\text{IL}}$, R/\overline{W} is a "don't care". Likewise, the right port interrupt flag ($\overline{\text{INTR}}$) is asserted when the left port writes to memory location 3FF (HEX) and to clear the interrupt flag ($\overline{\text{INTR}}$), the right port must access the memory location 3FF. The message (8 bits)

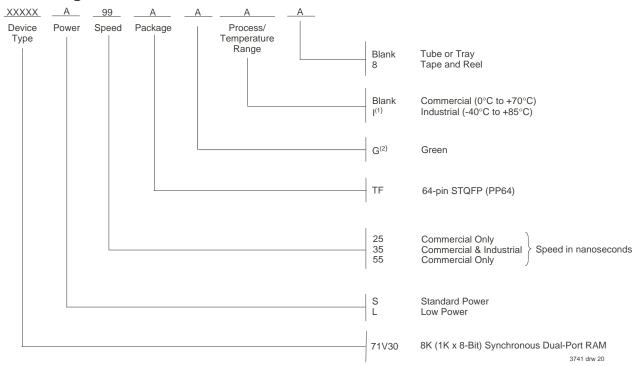
at 3FE or 3FF is user-defined, since it is an addressable SRAM location. If the interrupt function is not used, address locations 3FE and 3FF are not used as mail boxes, and are part of the random access memory. Refer to Table II for the interrupt operation.

Busy Logic

Busy Logic provides a hardware indication that both ports of the SRAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the SRAM is "Busy". The BUSY pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a BUSY indication, the write signal is gated internally to prevent the write from proceeding.

The use of \overline{BUSY} logic is not required or desirable for all applications. In some cases it may be useful to logically OR the \overline{BUSY} outputs together and use any \overline{BUSY} indication as an interrupt source to flag the event of an illegal or illogical operation.

Ordering Information



NOTES:

- 1. Industrial temperature range is available. For specific speeds, packages and powers contact your sales office.
- Green parts available. For specific speeds, packages and powers contact your sales office. LEAD FINISH (SnPb) parts are in EOL process. Product Discontinuation Notice - PDN# SP-17-02

Datasheet Document History

12/9/98: Initiated datasheet document history

Converted to new format

Cosmetic and typographical corrections Added additional notes to pin configurations

6/15/99: Changed drawing format

8/3/99: Page 2 Fixed typographical error

9/1/99: Removed Preliminary 11/12/99: Replaced IDT logo

1/17/01: Pages 1 and 2 Moved all of "Description" to page 2 and adjusted page layouts

Page 3 Increased storage temperature parameters

Clarified Taparameter

Page 4 DC Electrical parameters-changed wording from "open" to "disabled"

Changed ±200mV to 0mV in notes

3/14/05: Page 1 Added green availability to features

Page 17 Added green indicator to ordering information Page 1 & 17 Replaced old ™ logo with new ™ logo

7/16/07: Page 3 Added Junction Temperature spec values to the Absolute Maximum Rating table

 $Added \, footnote \, 3 \, for \, additional \, clarification \, of \, Junction \, Temperature$

Datasheet Document History (con't)

10/23/08: Page 14 Removed "IDT" from orderable part number

11/25/09: In order to correct the DC Chars table for the 71V30L35 speed grade and to the Data Retention Chars table, I Temp

values have been added to each table respectively. In addition, all of the AC tables and the ordering information also

now reflect this I temp correction

06/22/15: Page 2 Removed IDT in reference to fabrication

> Page 2 & 14 The package code PP64-1 changed to PP64 to match standard package codes

Page 14 Added Tape and Reel indicator to Ordering Information

07/23/15: Entire datasheet Removed the 55ns Industrial speed offering. 55ns speed only offered in commercial grade

Product Discontinuation Notice - PDN# SP-17-02 12/20/17:

Last time buy expires June 15, 2018



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 71V30S35TF
 71V30S25TF8
 71V30L35TFGI8
 71V30L55TF
 71V30S55TFG8
 71V30L25TFB
 71V30L35TFI

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